

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-21 (Cancelled)

22. (Currently Amended) A polycide gate structure, comprising:

(1) a polysilicon structure formed upon a substrate and having ~~laterals~~ first lateral side walls;

(2) an insulating structure ~~disposed~~ formed on said ~~laterals~~ first lateral side walls of said polysilicon structure for insulating said polysilicon structure;

(3) a silicide structure ~~formed entirely covering upon~~ said polysilicon structure and having ~~laterals~~ second lateral side walls; and

(4) a protecting structure formed by means of chemical vapor deposition (CVD) on said ~~laterals~~ second lateral side walls of said ~~silicide structure~~ for protecting said silicide structure.

23. (Previously Presented) The structure as claimed in claim 22, wherein said insulating structure is silicon dioxide (SiO₂).

24. (Previously Presented) The structure as claimed in claim 22, wherein said silicide structure upon said polysilicon structure comprises a barrier, a tungsten layer and a silicon nitride (SiNX) layer in sequence.

25. (Original) The structure as claimed in claim 24, wherein said barrier is titanium nitride (TiN).

26. (Cancelled)

27. (Previously Presented) The structure as claimed in claim 22, wherein said protecting structure has a thickness ranged from 50 to 500 Å.

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28. (Previously Presented) The structure as claimed in claim 22, wherein said protecting structure is silicon nitride (SiNX).
29. (Previously Presented) The structure method as claimed in claim 22, wherein said polysilicon structure is defined via an anisotropic dry etcher.
30. (Original) The structure as claimed in claim 22, wherein said insulating structure is formed by means of a dry oxidation method.
31. (Previously Presented) The structure as claimed in claim 22, wherein said silicide structure is defined via anisotropic dry etcher.
32. (Original) The structure as claimed in claim 22, wherein said protecting structure is defined via an anisotropic dry etcher.

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